

## 04CN10N-VB TO262 Datasheet

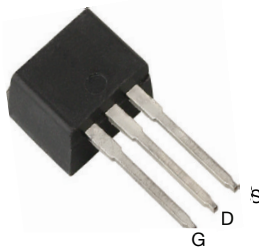
### N-Channel 100 V (D-S) 175 °C MOSFET

**PRODUCT SUMMARY**

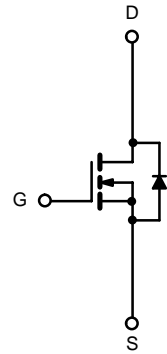
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.004 at $V_{GS} = 10$ V	110 <sup>a</sup>

**FEATURES**

- Trench Power MOSFET
- New Package with Low Thermal Resistance
- 100 %  $R_g$  Tested


**RoHS**  
 COMPLIANT
**TO-262**

Top View



N-Channel MOSFET

**ABSOLUTE MAXIMUM RATINGS**  $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175\text{ }^{\circ}\text{C}$ )	$I_D$	110 <sup>a</sup>	A
		87 <sup>a</sup>	
Pulsed Drain Current	$I_{DM}$	440	
Avalanche Current	$I_{AR}$	75	
Repetitive Avalanche Energy <sup>b</sup>	$E_{AR}$	280	mJ
Maximum Power Dissipation <sup>b</sup>	$P_D$	375 <sup>c</sup>	W
		3.75	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	$^{\circ}\text{C}$

**THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	$R_{thJA}$	40	$^{\circ}\text{C/W}$
Junction-to-Case (Drain)	$R_{thJC}$	0.4	

Notes:

a. Package limited.

b. Duty cycle  $\leq 1\%$ .

c. See SOA curve for voltage derating.

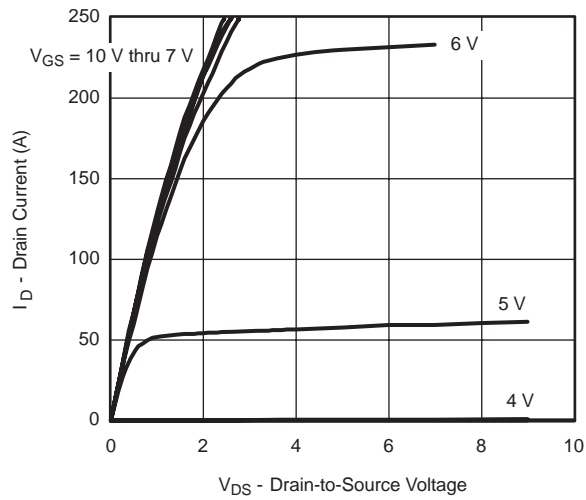
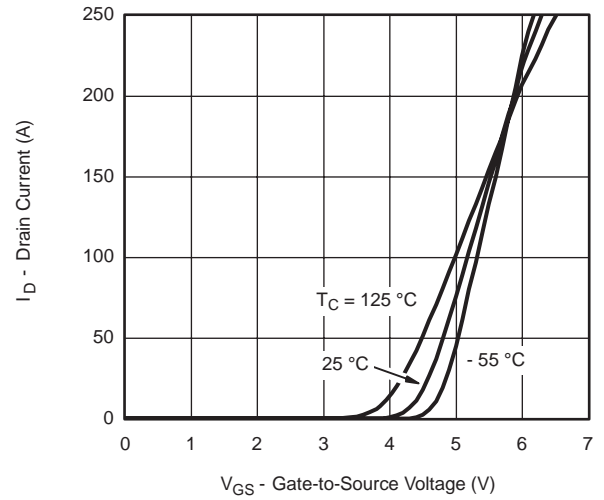
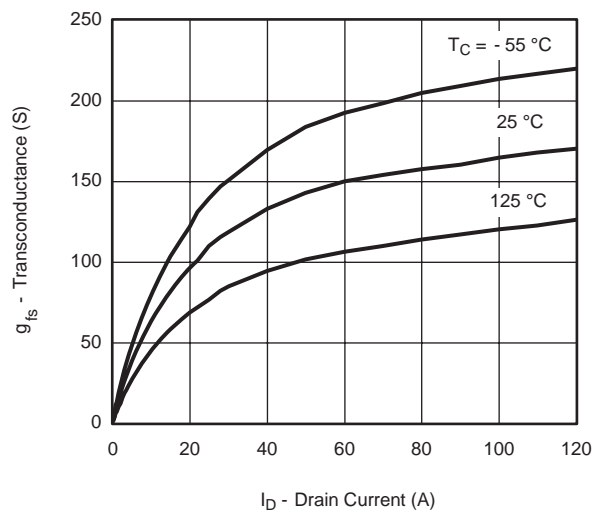
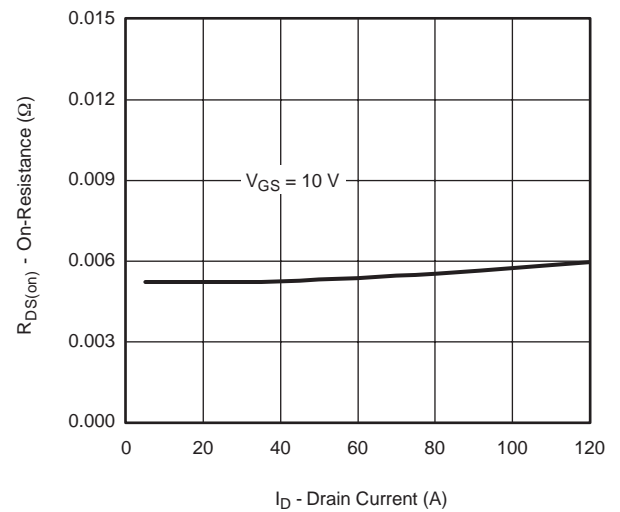
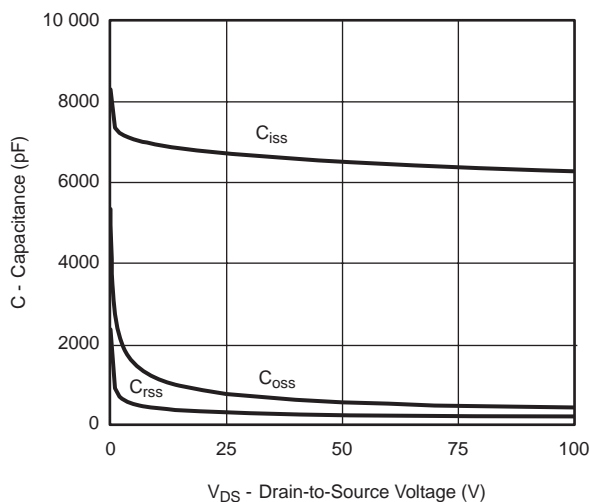
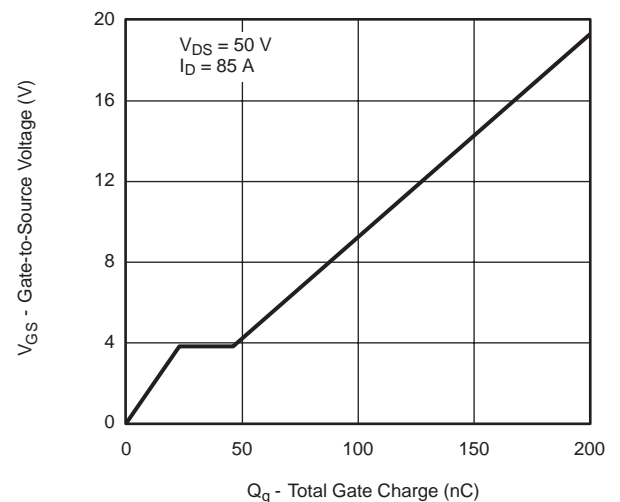
d. When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.004		$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.017		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.025		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	25			S
Dynamic <sup>b</sup>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6700		pF
Output Capacitance	$C_{oss}$			750		
Reverse Transfer Capacitance	$C_{rss}$			280		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$		110	160	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			24		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			24		
Gate Resistance	$R_g$		1.0		6.2	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		20	30	ns
Rise Time <sup>c</sup>	$t_r$			125	200	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			55	85	
Fall Time <sup>c</sup>	$t_f$			130	195	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}^b$						
Continuous Current	$I_S$				110	A
Pulsed Current	$I_{SM}$				240	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 85\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 50\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		70	140	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$			5.5	10	A
Reverse Recovery Charge	$Q_{rr}$			0.19	0.35	$\mu\text{C}$

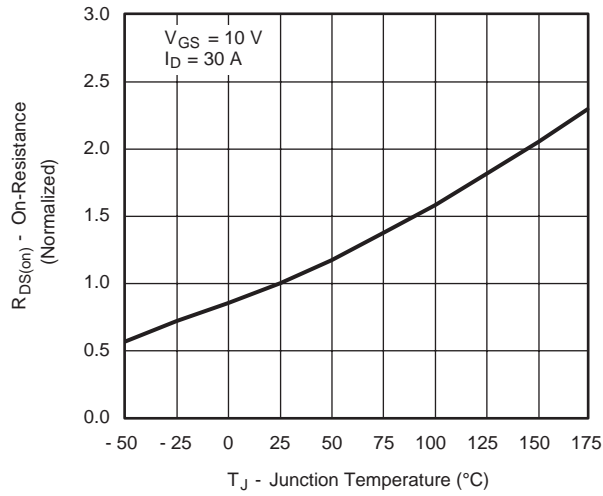
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

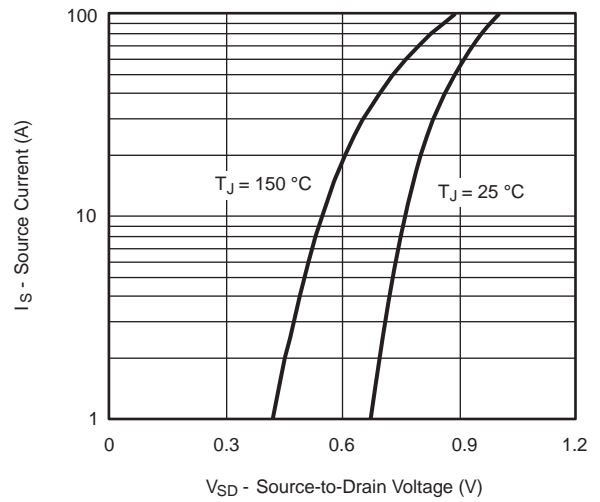
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

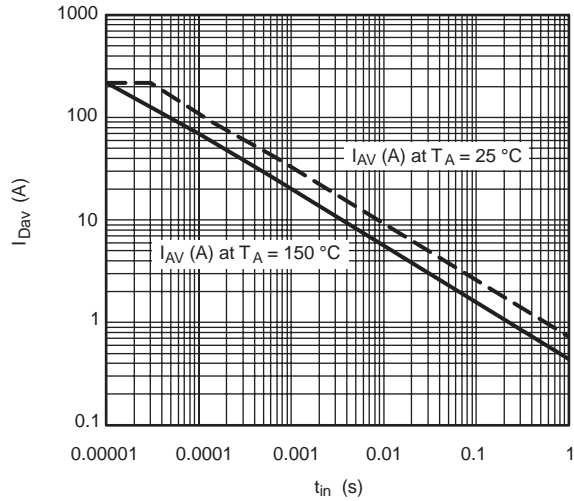
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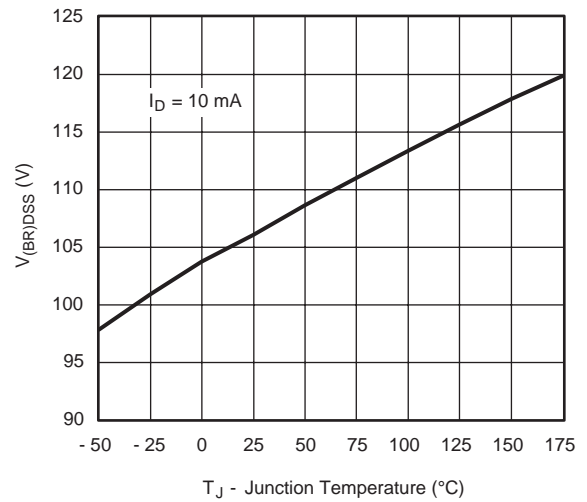
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**

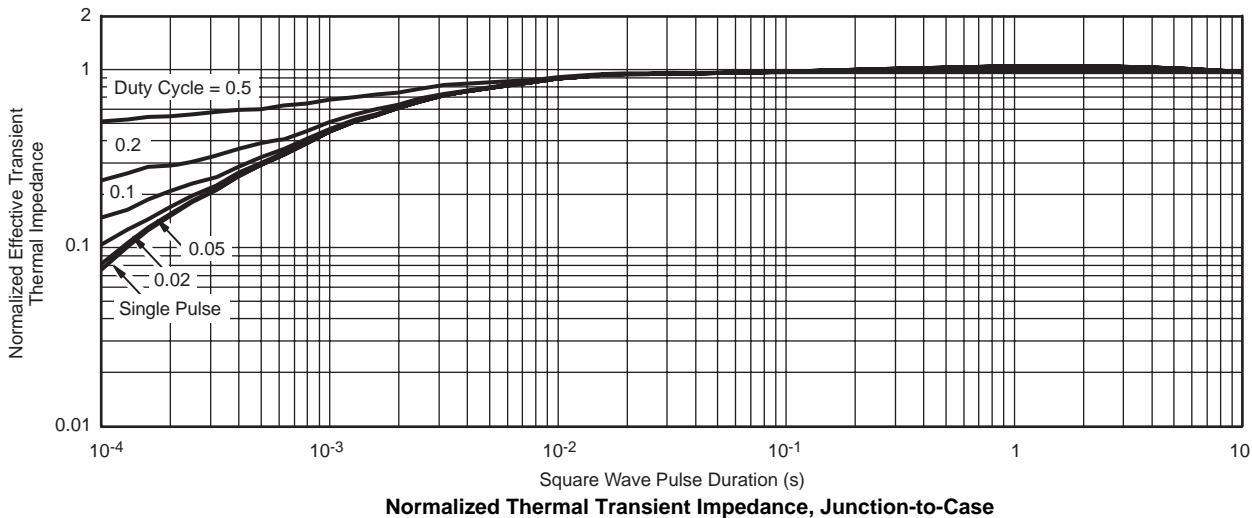
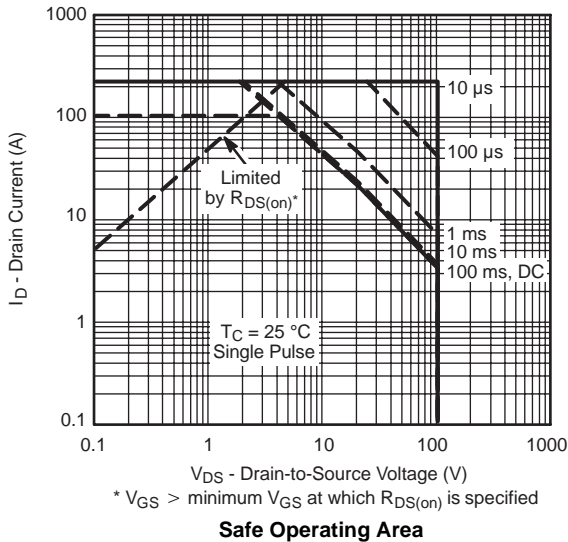


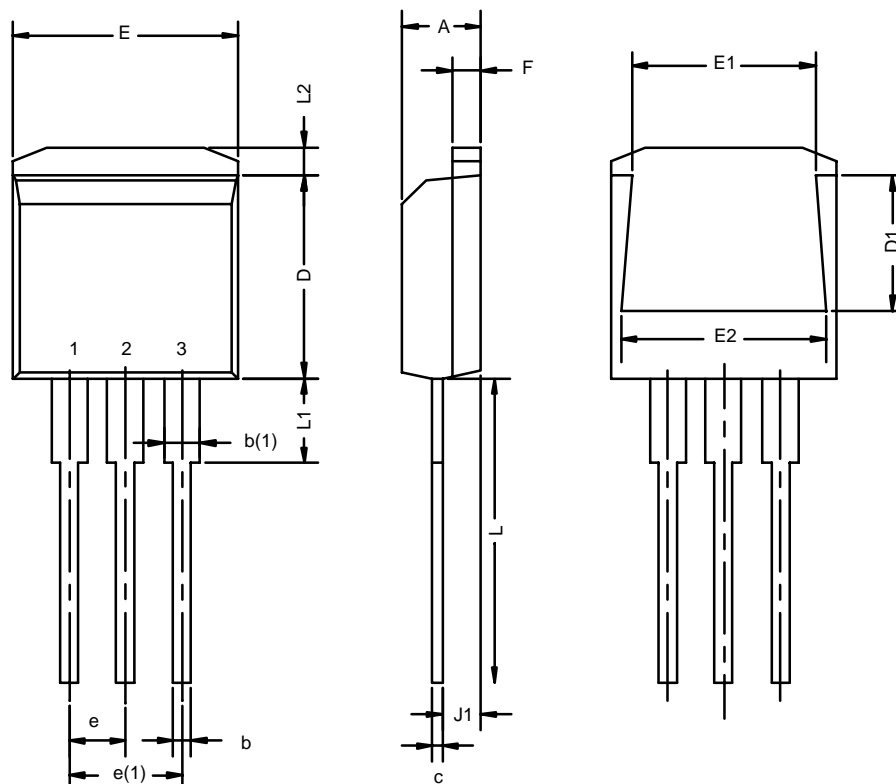
**Avalanche Current vs. Time**



**Drain Source Breakdown vs. Junction Temperature**

**THERMAL RATINGS**



**TO-262: 3-LEAD**

Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
<b>A</b>	4.32	4.70	0.170	0.185
<b>b</b>	0.64	1.00	0.025	0.039
<b>b(1)</b>	1.14	1.40	0.045	0.055
<b>c</b>	0.36	0.50	0.014	0.020
<b>D</b>	8.64	9.65	0.340	0.380
<b>D1</b>	5.59	6.10	0.220	0.240
<b>e</b>	2.41	2.67	0.095	0.105
<b>e(1)</b>	4.95	5.33	0.195	0.210
<b>E</b>	10.03	10.41	0.395	0.410
<b>E1</b>	7.87	8.64	0.310	0.340
<b>E2</b>	9.02	9.53	0.355	0.375
<b>F</b>	1.14	1.40	0.045	0.055
<b>J1</b>	2.41	2.79	0.095	0.110
<b>L</b>	13.08	14.22	0.515	0.560
<b>L1</b>	-	3.81	-	0.150
<b>L2</b>	1.02	1.40	0.040	0.055
ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855				

\*Use millimeters as the primary measurement

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